

In the Specification

Please amend paragraph 0018 as follows:

First, for the pattern for monitoring the depth of the STI 50, non-trench-etched active regions 10 are formed. The space between the active regions in the pattern for monitoring depth after the STI 50 is formed with unequal spacing to monitor precisely while sampling a pattern for measuring electrical effects by the depth and profile of the STI 60. Next, the pattern for measuring electrical effects by the depth and profile of the STI 60 is formed as described below. First, a plurality of non-trench-etched active regions 11 is formed. The spacing between the active regions 11 is preferably equal. Second, trench-etched regions 30 are formed. Third, a plurality of contact regions 20 for electrical interconnections between the active regions 11 is formed. Finally, a plurality of gates 40 for the transistor generation is formed.